



## FAST RECTIFIER DIODE

### DF141-80

<ul style="list-style-type: none"> <li>◆ <math>V_{RRM} = \underline{400-1600\text{ V}}</math></li> <li>◆ <math>I_{F(AV)} = \underline{80\text{ A}}</math> (<math>T_C = 79^\circ\text{C}</math>)</li> <li>◆ <math>I_{FSM} = \underline{2,5\text{ kA}}</math> (<math>t_p = 10\text{ms}</math>)</li> </ul>		
<ul style="list-style-type: none"> <li>◆ Small recovered time and charge</li> <li>◆ Acceptable for series and parallel connections (low dispersion <math>Q_{rr}</math>, <math>V_{FM}</math>, <math>I_{RRM}</math>)</li> </ul>		

#### MAXIMUM RATED VALUES

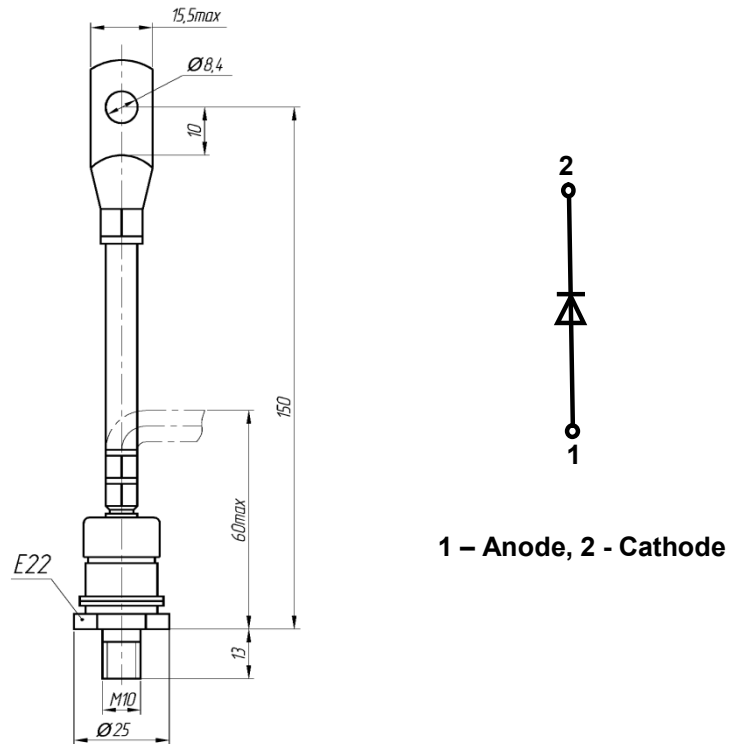
Parameter and conditions	Symbol	Values	Units
Repetitive peak reverse voltage, $T_j = -60 \dots +150\text{ }^\circ\text{C}$	$V_{RRM}$	400-1600	V
Non- repetitive peak reverse voltage, $T_j = -60 \dots +150\text{ }^\circ\text{C}$	$V_{RSM}$	500-1700	
Repetitive peak reverse current, $T_j = 150\text{ }^\circ\text{C}$ , $V_R = V_{RRM}$	$I_{RRM}$	30	mA
Maximum average forward current, $T_C = 79\text{ }^\circ\text{C}$ , $f = 50\text{ Hz}$	$I_{F(AV)}$	80	A
RMS forward current, $T_C = 79\text{ }^\circ\text{C}$ , $f = 50\text{ Hz}$	$I_{FRMS}$	125	
Surge non-repetitive current, $T_j = 150\text{ }^\circ\text{C}$ , $V_R = 0$ , $t_p = 10\text{ ms}$	$I_{FSM}$	2,5	kA
Safety factor	$I^2t$	$31,25 \cdot 10^3$	$\text{A}^2\text{s}$
Operation junction temperature range	$T_j$	-60 ... +150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-60 ... +50	

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<b>ELECTRICAL CHARACTERISTICS</b>					
Parameter and conditions	Symbol	Values			Units
		min	typ.	max	
Maximum peak forward voltage, $T_j = 25\text{ °C}$ , $I_F = 250\text{ A}$	$V_{FM}$	-	-	1,98	V
On-state threshold voltage, $T_j = 150\text{ °C}$ , $I_F = 125 - 380\text{ A}$	$V_{TO}$	-	-	1,10	
On-state slope resistance, $T_j = 150\text{ °C}$ , $I_F = 125 - 380\text{ A}$	$r_T$	-	-	4,4	mΩ
Reverse recovery time $T_j = 150\text{ °C}$ , $I_F = 80\text{ A}$ , $di_F/dt = -50\text{ A}/\mu\text{s}$ , $V_R \geq 100\text{ V}$	$t_{rr}$	-	-	1,6	μs
<b>THERMAL PARAMETERS</b>					
Thermal resistance junction to case, DC per diode anode side cooled	$R_{th(j-c)}$	-	-	0,45	°C/W
Thermal resistance case to heatsink, single side cooled	$R_{th(c-h)}$	-	-	0,10	
<b>MECHANICAL PARAMETERS</b>					
Weight	w	-	0,09	-	kg
Torque	Md	6	-	10	Nm



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**Fig. 1. Device Outline Drawing**  
(dimensions in mm)



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